TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U-MOSIII)

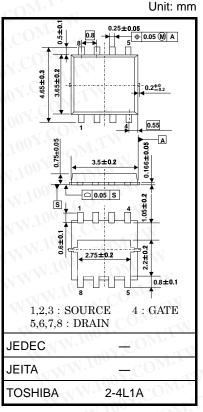
## **TPCM8001-H**

High-Efficiency DC / DC Converter Applications Notebook PC Applications Portable-Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 6.0 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) = 7 m $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 36 S$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th} = 1.1$  to 2.3 V ( $V_{DS} = 10$  V,  $I_{D} = 1$  mA)

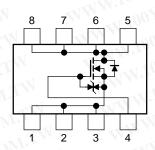
### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage	ONITW	V <sub>DSS</sub>	30	V-V
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$	$V_{DGR}$	30	V
Gate-source voltage	WILLES.	V <sub>GSS</sub>	±20	V
Drain current	DC (Note 1)	I <sub>D</sub>	20	Α
Diairi current	Pulsed (Note 1)	I <sub>DP</sub>	60	CO
Drain power dissipat	ion (Tc=25°C)	P <sub>D</sub>	30	W
Drain power dissipat	ion (t = 10 s) (Note 2a)	P <sub>D</sub>	2.3	W
Drain power dissipati	ion (t = 10 s) (Note 2b)	P <sub>D</sub>	1.0	W
Single-pulse avalance	he energy (Note 3)	E <sub>AS</sub>	104	mJ
Avalanche current	NW.100	I <sub>AR</sub>	20	( A
Repetitive avalanche	e energy Fc=25°C) (Note 4)	E <sub>AR</sub>	1.8	mJ
Channel temperature	1007	T <sub>ch</sub>	150	°C
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C



Weight: 0.028 g (typ.)

#### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

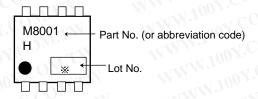
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

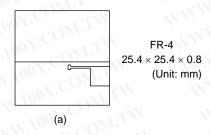
#### **Thermal Characteristics**

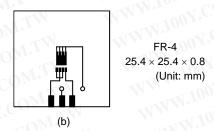
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Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R <sub>th</sub> (ch-c)	4.17	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	54.3	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

#### Marking (Note 5)



- Note 1: The channel temperature should not exceed 150°C during use.
- Note 2: (a) Device mounted on a glass-epoxy board (a)
- (b) Device mounted on a glass-epoxy board (b)

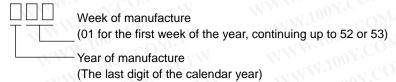




Note 3:  $V_{DD}=24~V,~T_{ch}=25^{\circ}C$  (initial),  $L=0.2~mH,~R_{G}=25~\Omega,~I_{AR}=20~A$ 

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- Note 4: Repetitive rating: pulse width limited by max channel temperature
- Note 5: on the lower left of the marking indicates Pin 1.
  - \* Weekly code: (Three digits)



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#### **Electrical Characteristics (Ta = 25°C)**

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Ur
Gate leakage cui	rent	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	N <del>er</del>	_	±10	μ
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	- TV	_	10	μ
Droin agurag bro	akdawa valtaga	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30		_	
Drain-source bre	akdown voitage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	- T	_	V
Gate threshold ve	oltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.1	- N	2.3	V
Droin source ON	raciatanaa	D- cold	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	a <del>o</del> M	10	14	mi
Drain-source ON	-resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		7	9.5	mg
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A	18	36	_	S
Input capacitance	WWW I	C <sub>iss</sub>	WWW.	N.C.	1130	N-	
Reverse transfer	capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	O <del>T.</del> C	120	W+	pF
Output capacitan	ce	C <sub>oss</sub>	OW. I	<u> </u>	480		
100X.COM	Rise time	WW.1007.		1002	2.5	V.LA	
Switching time	Turn-on time	ton	V <sub>GS</sub> 10 V I <sub>D</sub> = 10A V <sub>OUT</sub>	N.±00	9	MIT	N ns
Switching time	Fall time	tf	R <sub>L</sub> = 1.	M.70	3 C	$0\overline{M}$	CM
MM.100X.	Turn-off time	t <sub>off</sub>	$V_{DD} \simeq 15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10  \mu\text{s}$		19	CON	TV
Total gate charge	OMIT	OXIV	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	- <del>- 1</del>	19	o CO	1.
(gate-source plus	gate-drain)	$Q_{g}$	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		11	7.00	M.
Gate-source cha	rge 1	Q <sub>gs1</sub>	N.100Y.COM.TW	<u> </u>	3.9	07	nC
Gate-drain ("Mille	er") charge	Q <sub>gd</sub>	$V_{DD} \simeq 24 \text{ V}, \ V_{GS} = 10 \text{ V}, \ I_D = 20 \text{ A}$	<u> </u>	4.0	$00\overline{\lambda}$	
Gate switch char	ge CO	Q <sub>SW</sub>	W. TY	-11	6.0	CON.	

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# Source-Drain Ratings and Characteristics (Ta = 25°C)

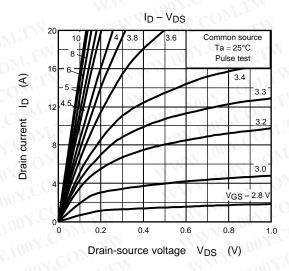
Characte	ristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I <sub>DRP</sub>	MAN TONT CONT.	_		60	Α
Forward voltage (diode)	1003:00	V <sub>DSF</sub>	I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V	IN _		-1.2	1 V

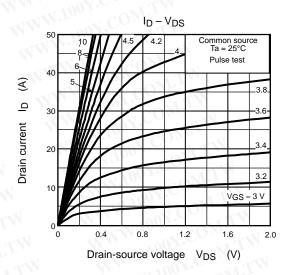
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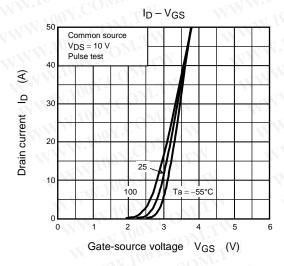
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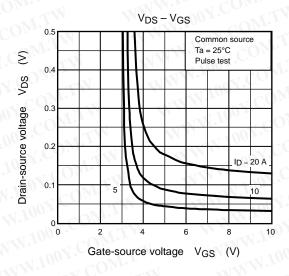
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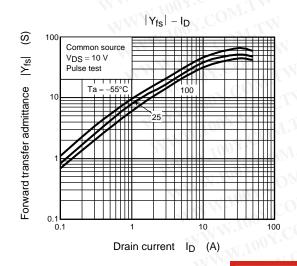
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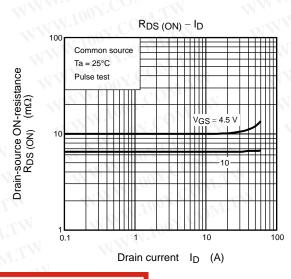




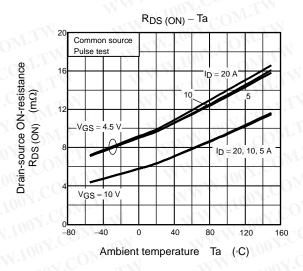


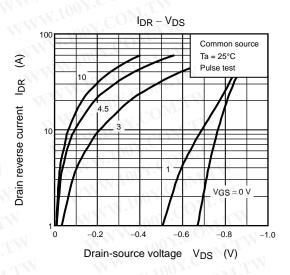


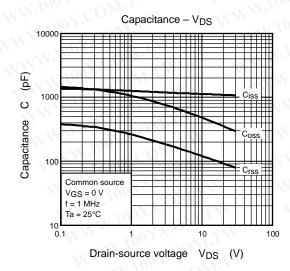


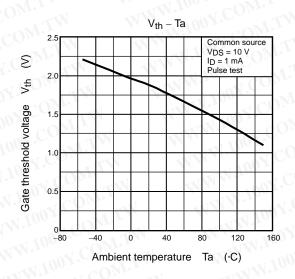


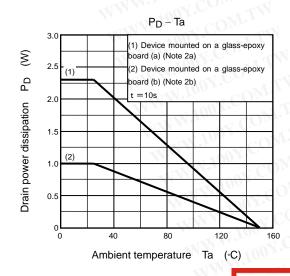
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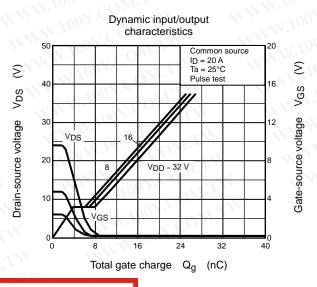




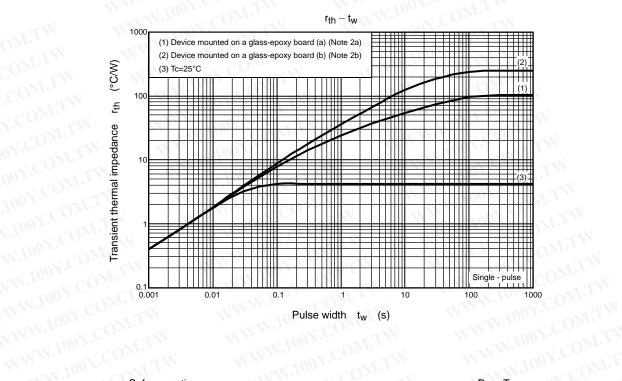


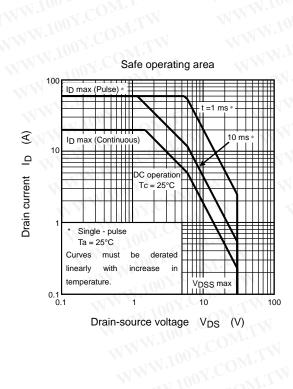






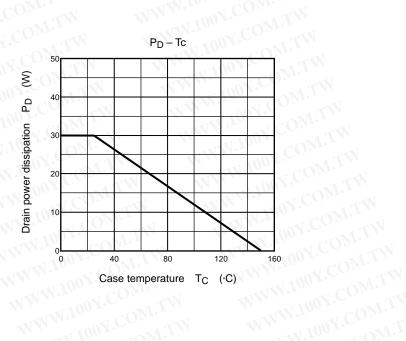
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